

ABSTRACT

The present invention aims at offering the semiconductor device which can improve the strength to the stress generated with a bonding pad. In the semiconductor device concerning the present invention, a plurality of bonding pads are formed on a semiconductor chip. In each bonding pad, a plurality of second line-like metals are formed under the first metal formed using the wiring layer of the top layer. And a bonding pad is put in order and located along the long-side direction of a second metal to achieve the above objects. That is, a bonding pad is put in order and located so that the long-side direction of a second metal and the arrangement direction of a bonding pad may become in the same direction.